Customer No.: 31561
Application No.: 10/709,306
Docket No.: 12952-US-PA

AMENDMENT

Please amend the application as indicated hereafter.

In the Claims:

1. (currently amended) A pixel structure, comprising:

a scan line, disposed over a substrate;

a redundant scan line, disposed over the scan line;

a dielectric layer, disposed between the scan line and the redundant scan line, wherein more than three first contact holes are formed in the dielectric layer, wherein the scan line is electrically connected with the redundant scan line through at least one or more first contact holes that expose a portion of the scan line, wherein each first contact hole has a length in a range of about 20um to about a length of the scan line;

an active component, disposed adjacent to the scan line; and

a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line to write an image signal to the pixel electrode.

2. (previously presented) The pixel structure of claim 1, further comprising:

a data line, disposed over the substrate; and

a redundant data line, disposed under the data line, wherein the dielectric layer is disposed between the data line and the redundant data line, and the dielectric layer further comprises more than three second contact holes, wherein the data line is electrically

connected with the redundant data line through at least one or more second contact holes that expose a portion of the redundant data line.

3. (previously presented) The pixel structure of claim 1, further comprising:

a data line, disposed over the substrate; and

a redundant data line, disposed under the data line, wherein the dielectric layer is disposed between the data line and the redundant data line, and a third contact hole having a size in a range of about 20um to about a length of the data line is formed in the dielectric layer through which the data line is electrically connected with the redundant data line.

4. (original) The pixel structure of claim 3, wherein the third contact hole comprises a rectangular hole, and a length of the rectangular hole is in a range of about 20um to about a length of the data line.

5. (original) The pixel structure of claim 3, wherein the active component comprises a thin film transistor (TFT).

6. (currently amended) A pixel structure, comprising:

a scan line, disposed over a substrate;

a redundant scan line, disposed over the scan line;

a dielectric layer, disposed between the scan line and the redundant scan line, wherein more than three first contact holes are formed in the dielectric layer, wherein the scan line is electrically connected with the redundant scan line through at least one or more first contact holes that expose a portion of the scan line, wherein the first contact holes have a length in a range of about 20um to about a length of the scan line;

a data line, disposed over the substrate;

an active component, disposed adjacent to an intersection of the scan line and the data line; and

a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line ~~control~~ to write an image signal transmitted by the data line to the pixel electrode.

Claim 7 (canceled).

8. (previously presented) The pixel structure of claim 6, further comprising:

a redundant data line, disposed under the data line, wherein the dielectric layer is disposed between the data line and the redundant data line, and at least three second contact holes are formed in the dielectric layer, wherein the data line is electrically connected with the redundant data line through at least one or more second contact holes that expose a portion of the redundant data line.

9. (original) The pixel structure of claim 6, further comprising:

a redundant data line, disposed under the data line, wherein the dielectric layer is disposed between the data line and the redundant data line between, and a third contact hole having a size in a range of about 20um to about a length of the data line through which the dielectric layer the data line is electrically connected with the redundant data line.

10. (original) The pixel structure of claim 9, wherein the third contact hole comprises a rectangular hole having a length in a range of about 20um to about a length of the data line.

11. (original) The pixel structure of claim 6, wherein the active component comprises a thin film transistor (TFT).

Claim 12-13 (canceled).

14. (currently amended) A pixel structure, comprising:

a scan line, disposed over a substrate;

a data line, disposed over the substrate;

a redundant data line, disposed under the data line;

a dielectric layer, disposed between the data line and the redundant data line, wherein a first contact hole having a size in a range of about 20um to about a length of the data line is formed in the dielectric layer through which the data line is electrically connected with the redundant data line;

an active component, disposed adjacent to an intersection of the scan line and the data line; and

a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line ~~control~~ to write an image signal transmitted by the data line to the pixel electrode.

15. (original) The pixel structure of claim 14, wherein the first contact hole comprises a rectangular hole having a length in a range of about 20um.

16. (original) The pixel structure of claim 14, wherein the active component comprises a thin film transistor (TFT).